

Features

- Single Voltage Read/Write Operation: 2.65V to 3.3V (BV), 3.0V to 3.6V (LV)
- Access Time – 70 ns
- Sector Erase Architecture
 - Thirty-one 32K Word (64K Bytes) Sectors with Individual Write Lockout
 - Eight 4K Word (8K Bytes) Sectors with Individual Write Lockout
- Fast Word Program Time – 20 μ s
- Fast Sector Erase Time – 300 ms
- Dual-plane Organization, Permitting Concurrent Read while Program/Erase
 - Memory Plane A: Eight 4K Word and Seven 32K Word Sectors
 - Memory Plane B: Twenty-four 32K Word Sectors
- Erase Suspend Capability
 - Supports Reading/Programming Data from Any Sector by Suspending Erase of Any Different Sector
- Low-power Operation
 - 30 mA Active
 - 10 μ A Standby
- Data Polling, Toggle Bit, Ready/ $\overline{\text{Busy}}$ for End of Program Detection
- VPP Pin for Accelerated Program/Erase Operations
- $\overline{\text{RESET}}$ Input for Device Initialization
- Sector Lockdown Support
- TSOP and CBGA Package Options
- Top or Bottom Boot Block Configuration Available
- 128-bit Protection Register

Description

The AT49BV/LV16X4A(T) is a 2.65- to 3.3-volt 16-megabit Flash memory organized as 1,048,576 words of 16 bits each or 2,097,152 bytes of 8 bits each. The x16 data appears on I/O0 - I/O15; the x8 data appears on I/O0 - I/O7. The memory is divided into 39 sectors for erase operations. The device is offered in 48-lead TSOP and 48-ball CBGA packages. The device has $\overline{\text{CE}}$ and $\overline{\text{OE}}$ control signals to avoid any bus contention. This device can be read or reprogrammed using a single 2.65V power supply, making it ideally suited for in-system programming.

Pin Configurations

| Pin Name | Function |
|-------------------------------|-------------------------------------------------------------------------|
| A0 - A19 | Addresses |
| $\overline{\text{CE}}$ | Chip Enable |
| $\overline{\text{OE}}$ | Output Enable |
| $\overline{\text{WE}}$ | Write Enable |
| $\overline{\text{RESET}}$ | Reset |
| RDY/ $\overline{\text{BUSY}}$ | READY/ $\overline{\text{BUSY}}$ Output |
| VPP | Power Supply for Accelerated Program/Erase Operations |
| I/O0 - I/O14 | Data Inputs/Outputs |
| I/O15 (A-1) | I/O15 (Data Input/Output, Word Mode) A-1 (LSB Address Input, Byte Mode) |
| BYTE | Selects Byte or Word Mode |
| NC | No Connect |
| VCCQ | Output Power Supply |



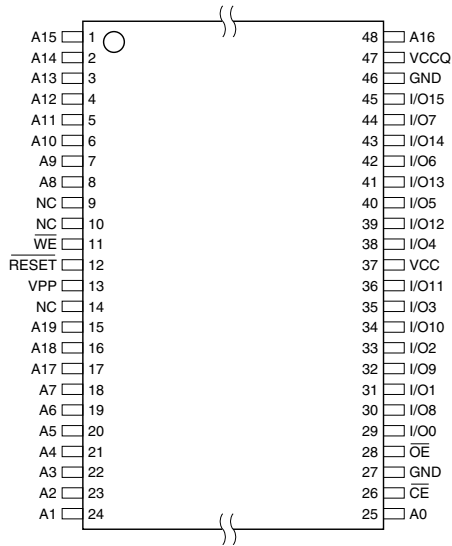
**16-megabit
(1M x 16/2M x 8)
3-volt Only
Flash Memory**

**AT49BV1604A
AT49BV1604AT
AT49BV1614A
AT49LV1614A
AT49BV1614AT
AT49LV1614AT**

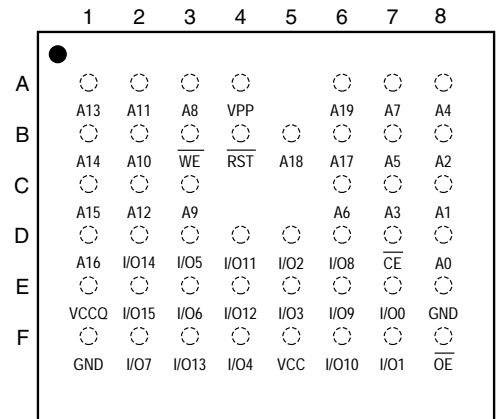




TSOP Top View

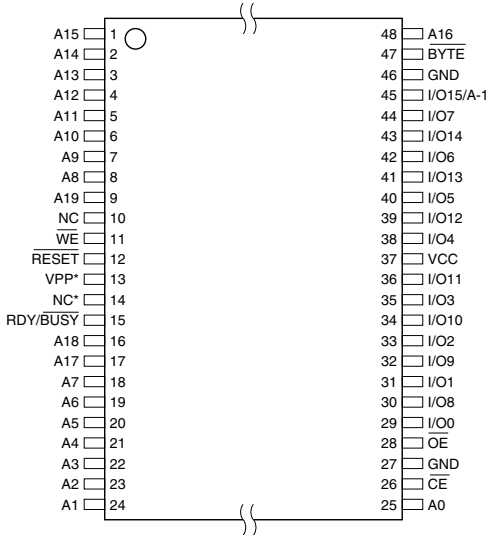


CBGA Top View (Ball Down)

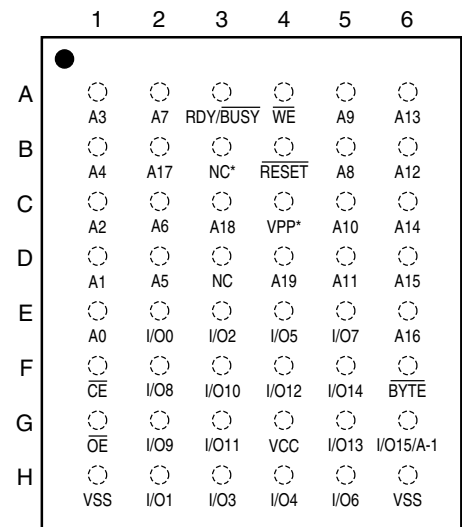


← AT49BV1604A(T) →

TSOP Top View
Type 1



CBGA Top View



← AT49BV/LV1614A(T) →

Note: *For the AT49BV/LV1614A(T), either pin 13 or pin 14 (TSOP package) or ball B3 or ball C4 (CBGA package) can be connected to V_{PP} or both pins can be unconnected. Accelerated program/erase operations are only achieved if a voltage of $5V \pm 0.5V$ or $12V \pm 0.5V$ is applied to pin 13 (TSOP package) or ball C4 (CBGA package).

The device powers on in the read mode. Command sequences are used to place the device in other operation modes such as program and erase. The device has the capability to protect the data in any sector (see Sector Lockdown section).

The device is segmented into two memory planes. Reads from memory plane B may be performed even while program or erase functions are being executed in memory plane A and vice versa. This operation allows improved system performance by not requiring the system to wait for a program or erase operation to complete before a read is performed. To further increase the flexibility of the device, it contains an Erase Suspend feature. This feature will put the erase on hold for any amount of time and let the user read data from or program data to any of the remaining sectors within the same memory plane. There is no reason to suspend the erase operation if the data to be read is in the other memory plane. The end of a program or an erase cycle is detected by the Ready/Busy pin, Data Polling or by the toggle bit.

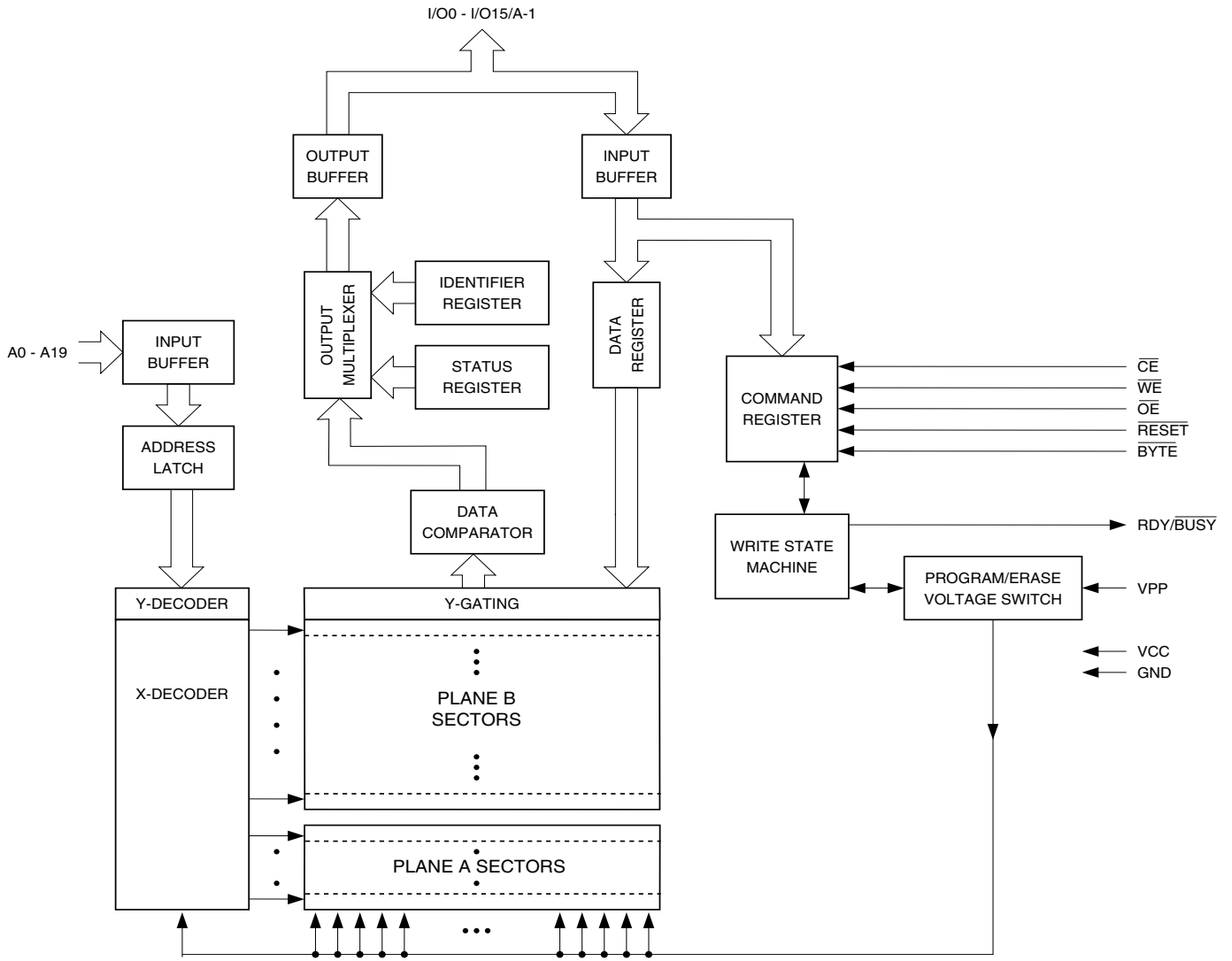
The VPP pin provides faster program/erase times. With V_{PP} at 5.0V or 12.0V, the program and erase operations are accelerated.

A six-byte command (Enter Single Pulse Program Mode) sequence to remove the requirement of entering the three-byte program sequence is offered to further improve programming time. After entering the six-byte code, only single pulses on the write control lines are required for writing into the device. This mode (Single Pulse Byte/Word Program) is exited by powering down the device, or by pulsing the RESET pin low for a minimum of 500 ns and then bringing it back to V_{CC} . Erase and Erase Suspend/Resume commands will not work while in this mode; if entered they will result in data being programmed into the device. It is not recommended that the six-byte code reside in the software of the final product but only exist in external programming code.

When using the AT49BV1604A(T) pinout configuration, the device always operates in the word mode. In the AT49BV/LV1614A(T) configuration, the \overline{BYTE} pin controls whether the device data I/O pins operate in the byte or word configuration. If the \overline{BYTE} pin is set at logic "1", the device is in word configuration, I/O0 - I/O15 are active and controlled by \overline{CE} and \overline{OE} .

If the \overline{BYTE} pin is set at logic "0", the device is in byte configuration, and only data I/O pins I/O0 - I/O7 are active and controlled by \overline{CE} and \overline{OE} . The data I/O pins I/O8 - I/O14 are tri-stated, and the I/O15 pin is used as an input for the LSB (A-1) address function.

Block Diagram



Device Operation

READ: The AT49BV/LV16X4A(T) is accessed like an EPROM. When \overline{CE} and \overline{OE} are low and \overline{WE} is high, the data stored at the memory location determined by the address pins are asserted on the outputs. The outputs are put in the high-impedance state whenever \overline{CE} or \overline{OE} is high. This dual-line control gives designers flexibility in preventing bus contention.

COMMAND SEQUENCES: When the device is first powered on it will be reset to the read or standby mode, depending upon the state of the control line inputs. In order to perform other device functions, a series of command sequences are entered into the device. The command sequences are shown in the Command Definitions table (I/O8 - I/O15 are don't care inputs for the command codes). The command sequences are written by applying a low pulse on the \overline{WE} or \overline{CE} input with \overline{CE} or \overline{WE} low (respectively) and \overline{OE} high. The address is latched on the falling edge of \overline{CE} or \overline{WE} , whichever occurs last. The data is latched by the first rising edge of \overline{CE} or \overline{WE} . Standard microprocessor write timings are used. The address locations used in the command sequences are not affected by entering the command sequences.

RESET: A \overline{RESET} input pin is provided to ease some system applications. When \overline{RESET} is at a logic high level, the device is in its standard operating mode. A low level on the \overline{RESET} input halts the present device operation and puts the outputs of the device in a high-impedance state. When a high level is reasserted on the \overline{RESET} pin, the device returns to the read or standby mode, depending upon the state of the control inputs.

ERASURE: Before a byte/word can be reprogrammed, it must be erased. The erased state of memory bits is a logical "1". The entire device can be erased by using the Chip Erase command or individual sectors can be erased by using the Sector Erase command.

CHIP ERASE: The entire device can be erased at one time by using the six-byte chip erase software code. After the chip erase has been initiated, the device will internally time the erase operation so that no external clocks are required. The maximum time to erase the chip is t_{EC} .

If the sector lockdown has been enabled, the chip erase will not erase the data in the sector that has been locked out; it will erase only the unprotected sectors. After the chip erase, the device will return to the read or standby mode.

SECTOR ERASE: As an alternative to a full chip erase, the device is organized into 39 sectors (SA0 - SA38) that can be individually erased. The Sector Erase command is a six-bus cycle operation. The sector address is latched on the falling \overline{WE} edge of the sixth cycle while the 30H data input command is latched on the rising edge of \overline{WE} . The sector erase starts after the rising edge of \overline{WE} of the sixth cycle. The erase operation is internally controlled; it will automatically time to completion. The maximum time to erase a section is t_{SEC} . When the sector programming lockdown feature is not enabled, the sector will erase (from the same Sector Erase command). An attempt to erase a sector that has been protected will result in the operation terminating in 2 μ s.

BYTE/WORD PROGRAMMING: Once a memory block is erased, it is programmed (to a logical "0") on a byte-by-byte or on a word-by-word basis. Programming is accomplished via the internal device command register and is a four-bus cycle operation. The device will automatically generate the required internal program pulses.

Any commands written to the chip during the embedded programming cycle will be ignored. If a hardware reset happens during programming, the data at the location being programmed will be corrupted. Please note that a data "0" cannot be programmed back to a "1"; only erase operations can convert "0"s to "1"s. Programming is completed after the specified t_{BP} cycle time. The Data Polling feature or the Toggle Bit feature may be used to indicate the end of a program cycle.

VPP PIN: The circuitry of the AT49BV/LV16X4A(T) is designed so that the device can be programmed or erased from the V_{CC} power supply or from the VPP input pin. When V_{PP} is less than or equal to the VCC pin, the device selects the V_{CC} supply for programming and erase



operations. When the VPP pin is greater than the V_{CC} supply, the device will select the V_{PP} input as the power supply for programming and erase operations. The device will allow for some variations between the V_{PP} input and the V_{CC} power supply in its selection of V_{CC} or V_{PP} for program or erase operations. If the VPP pin is within 0.3V of V_{CC} for 2.65V < V_{CC} < 3.3V, then the program or erase operations will use V_{CC} and disregard the V_{PP} input signal. When the V_{PP} signal is used to accelerate program and erase operations, the V_{PP} must be in the 5V ± 0.5V or 12V ± 0.5V range to ensure proper operation. The V_{pp} pin can be left unconnected.

SECTOR LOCKDOWN: Each sector has a programming lockdown feature. This feature prevents programming of data in the designated sectors once the feature has been enabled. These sectors can contain secure code that is used to bring up the system. Enabling the lockdown feature will allow the boot code to stay in the device while data in the rest of the device is updated. This feature does not have to be activated; any sector's usage as a write protected region is optional to the user.

At power-up or reset all sectors are unlocked. To activate the lockdown for a specific sector, the six-bus cycle Sector Lockdown command must be issued. Once a sector has been locked down, the contents of the sector is read-only and cannot be erased or programmed.

SECTOR LOCKDOWN DETECTION: A software method is available to determine if programming of a sector is locked down. When the device is in the software product identification mode (see Software Product Identification Entry and Exit sections) a read from address location 00002H within a sector will show if programming the sector is locked down. If the data on I/O0 is low, the sector can be programmed; if the data on I/O0 is high, the program lockdown feature has been enabled and the sector cannot be programmed. The software product identification exit code should be used to return to standard operation.

SECTOR LOCKDOWN OVERRIDE: The only way to unlock a sector that is locked down is through reset or power-up cycles. After power-up or reset, the content of a sector that is locked down can be erased and reprogrammed.

ERASE SUSPEND/ERASE RESUME: The Erase Suspend command allows the system to interrupt a sector erase operation and then program or read data from a different sector within the same plane. Since this device has a dual-plane architecture, there is no need to use the Erase Suspend feature while erasing a sector when you want to read data from a sector in the other plane. After the Erase Suspend command is given, the device requires a maximum time of 15 μs to suspend the erase operation. After the erase operation has been suspended, the plane that contains the suspended sector enters the erase-suspend-read mode. The system can then read data or program data to any other sector within the device. An address is not required during the Erase Suspend command. During a sector erase suspend, another sector cannot be erased. To resume the sector erase operation, the system must write the Erase Resume command. The Erase Resume command is a one-bus cycle command, which does require the plane address (determined by A18 and A19). The device also supports an erase suspend during a complete chip erase. While the chip erase is suspended, the user can read from any sector within the memory that is protected. The command sequence for a chip erase suspend and a sector erase suspend are the same.

PRODUCT IDENTIFICATION: The product identification mode identifies the device and manufacturer as Atmel. It may be accessed by hardware or software operation. The hardware operation mode can be used by an external programmer to identify the correct programming algorithm for the Atmel product.

For details, see "Operating Modes" on page 12 (for hardware operation) or "Software Product Identification Entry/Exit" on page 20. The manufacturer and device codes are the same for both modes.

128-BIT PROTECTION REGISTER: The AT49BV/LV16X4A(T) contains a 128-bit register that can be used for security purposes in system design. The protection register is divided into two 64-bit blocks. The two blocks are designated as block A and block B. The data in block A is non-changeable and is programmed at the factory with a unique number. The data in block B is programmed by the user and can be locked out such that data in the block cannot be reprogrammed. To program block B in the protection register, the four-bus cycle Program Protection Register command must be used as shown in the Command Definition table on page 8. To lock out block B, the four-bus cycle Lock Protection Register command must be used as shown in the Command Definition table. Data bit D1 must be zero during the fourth bus cycle. All other data bits during the fourth bus cycle are don't cares. Please see the "Protection Register Addressing Table" on page 9 for the address locations in the protection register. To read the protection register, the Product ID Entry command is given followed by a normal read operation from an address within the protection register. After reading the protection register, the Product ID Exit command must be given prior to performing any other operation.

DATA POLLING: The AT49BV/LV16X4A(T) features $\overline{\text{Data}}$ Polling to indicate the end of a program cycle. During a program cycle an attempted read of the last byte/word loaded will result in the complement of the loaded data on I/O7. Once the program cycle has been completed, true data is valid on all outputs and the next cycle may begin. During a chip or sector erase operation, an attempt to read the device will give a "0" on I/O7. Once the program or erase cycle has completed, true data will be read from the device. $\overline{\text{Data}}$ Polling may begin at any time during the program cycle. Please see "Status Bit Table" on page 21 for more details.

TOGGLE BIT: In addition to $\overline{\text{Data}}$ Polling, the AT49BV/LV16X4A(T) provides another method for determining the end of a program or erase cycle. During a program or erase operation, successive attempts to read data from the same memory plane will result in I/O6 toggling between one and zero. Once the program cycle has completed, I/O6 will stop toggling and valid data will be read. Examining the toggle bit may begin at any time during a program cycle.

An additional toggle bit is available on I/O2, which can be used in conjunction with the toggle bit that is available on I/O6. While a sector is erase suspended, a read or a program operation from the suspended sector will result in the I/O2 bit toggling. Please see "Status Bit Table" on page 21 for more details.

RDY/ $\overline{\text{BUSY}}$: For the AT49BV/LV1614A(T), an open-drain Ready/ $\overline{\text{BUSY}}$ output pin provides another method of detecting the end of a program or erase operation. RDY/ $\overline{\text{BUSY}}$ is actively pulled low during the internal program and erase cycles and is released at the completion of the cycle. The open-drain connection allows for OR-tying of several devices to the same RDY/ $\overline{\text{BUSY}}$ line.

HARDWARE DATA PROTECTION: The Hardware Data Protection feature protects against inadvertent programs to the AT49BV/LV16X4A(T) in the following ways: (a) V_{CC} sense: if V_{CC} is below 1.8V (typical), the program function is inhibited. (b) V_{CC} power-on delay: once V_{CC} has reached the V_{CC} sense level, the device will automatically time out 10 ms (typical) before programming. (c) Program inhibit: holding any one of $\overline{\text{OE}}$ low, $\overline{\text{CE}}$ high or $\overline{\text{WE}}$ high inhibits program cycles. (d) Noise filter: pulses of less than 15 ns (typical) on the $\overline{\text{WE}}$ or $\overline{\text{CE}}$ inputs will not initiate a program cycle.

INPUT LEVELS: While operating with a 2.65V to 3.3V power supply, the address inputs and control inputs ($\overline{\text{OE}}$, $\overline{\text{CE}}$ and $\overline{\text{WE}}$) may be driven from 0 to 5.5V without adversely affecting the operation of the device. The I/O lines can only be driven from 0 to $V_{CC} + 0.6V$.

OUTPUT LEVELS: For the AT49BV1604A(T), output high levels (V_{OH}) are equal to $V_{CCQ} - 0.2V$ (not V_{CC}). For 2.65V - 3.3V output levels, V_{CCQ} must be tied to V_{CC} . For 1.8V - 2.2V output levels, V_{CCQ} must be regulated to $2.0V \pm 10\%$, while V_{CC} must be regulated to 2.65V - 3.0V (for minimum power).



Command Definition in Hex⁽¹⁾

| Command Sequence | Bus Cycles | 1st Bus Cycle | | 2nd Bus Cycle | | 3rd Bus Cycle | | 4th Bus Cycle | | 5th Bus Cycle | | 6th Bus Cycle | |
|------------------------------------|------------|-------------------|------------------|--------------------|------|---------------|------|---------------|---------------------------------|---------------|------|----------------------|------|
| | | Addr | Data | Addr | Data | Addr | Data | Addr | Data | Addr | Data | Addr | Data |
| Read | 1 | Addr | D _{OUT} | | | | | | | | | | |
| Chip Erase | 6 | 555 | AA | AAA ⁽²⁾ | 55 | 555 | 80 | 555 | AA | AAA | 55 | 555 | 10 |
| Sector Erase | 6 | 555 | AA | AAA | 55 | 555 | 80 | 555 | AA | AAA | 55 | SA ⁽³⁾⁽⁴⁾ | 30 |
| Byte/Word Program | 4 | 555 | AA | AAA | 55 | 555 | A0 | Addr | D _{IN} | | | | |
| Enter Single Pulse Program Mode | 6 | 555 | AA | AAA | 55 | 555 | 80 | 555 | AA | AAA | 55 | 555 | A0 |
| Single Pulse Byte/Word Program | 1 | Addr | D _{IN} | | | | | | | | | | |
| Sector Lockdown | 6 | 555 | AA | AAA | 55 | 555 | 80 | 555 | AA | AAA | 55 | SA ⁽³⁾⁽⁴⁾ | 60 |
| Erase Suspend | 1 | XXX | B0 | | | | | | | | | | |
| Erase Resume | 1 | PA ⁽⁵⁾ | 30 | | | | | | | | | | |
| Product ID Entry | 3 | 555 | AA | AAA | 55 | 555 | 90 | | | | | | |
| Product ID Exit ⁽⁶⁾ | 3 | 555 | AA | AAA | 55 | 555 | F0 | | | | | | |
| Product ID Exit ⁽⁶⁾ | 1 | XXX | F0 | | | | | | | | | | |
| Program Protection Register | 4 | 555 | AA | AAA | 55 | 555 | C0 | Addr | D _{IN} | | | | |
| Lock Protection Register - Block B | 4 | 555 | AA | AAA | 55 | 555 | C0 | 080 | X0 | | | | |
| Status of Block B Protection | 4 | 555 | AA | AAA | 55 | 555 | 90 | 80 | D _{OUT} ⁽⁷⁾ | | | | |

- Notes:
- The DATA FORMAT shown for each bus cycle is as follows; I/O7 - I/O0 (Hex). In word operation I/O15 - I/O8 are Don't Care. The ADDRESS FORMAT shown for each bus cycle is as follows: A11 - A0 (Hex). Address A19 through A11 are Don't Care in the word mode. Address A19 through A11 and A-1 are Don't Care in the byte mode.
 - Since A11 is a Don't Care, AAA can be replaced with 2AA.
 - SA = sector address. Any byte/word address within a sector can be used to designate the sector address (see pages 10 and 11 for details).
 - Once a sector is in the lockdown mode, data in the protected sector cannot be changed unless the chip is reset or power cycled.
 - PA is the plane address (A19-A18).
 - Either one of the Product ID Exit commands can be used.
 - If data bit D1 is "0", block B is locked. If data bit D1 is "1", block B can be reprogrammed.

Absolute Maximum Ratings*

| | |
|--------------------------------------------------------------------------------|---------------------------------|
| Temperature under Bias | -55°C to +125°C |
| Storage Temperature | -65°C to +150°C |
| All Input Voltages (including NC Pins) with Respect to Ground | -0.6V to +6.25V |
| All Output Voltages with Respect to Ground | -0.6V to V _{CC} + 0.6V |
| Voltage on \overline{OE} and V _{PP} with Respect to Ground | -0.6V to +13.0V |

*NOTICE: Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

Protection Register Addressing Table

| Word | Use | Block | A7 | A6 | A5 | A4 | A3 | A2 | A1 | A0 |
|------|---------|-------|----|----|----|----|----|----|----|----|
| 0 | Factory | A | 1 | 0 | 0 | 0 | 0 | 0 | 0 | 1 |
| 1 | Factory | A | 1 | 0 | 0 | 0 | 0 | 0 | 1 | 0 |
| 2 | Factory | A | 1 | 0 | 0 | 0 | 0 | 0 | 1 | 1 |
| 3 | Factory | A | 1 | 0 | 0 | 0 | 0 | 1 | 0 | 0 |
| 4 | User | B | 1 | 0 | 0 | 0 | 0 | 1 | 0 | 1 |
| 5 | User | B | 1 | 0 | 0 | 0 | 0 | 1 | 1 | 0 |
| 6 | User | B | 1 | 0 | 0 | 0 | 0 | 1 | 1 | 1 |
| 7 | User | B | 1 | 0 | 0 | 0 | 1 | 0 | 0 | 0 |

Note: 1. All address lines not specified in the above table must be 0 when accessing the protection register, i.e., A19 - A8 = 0.



AT49BV/LV1604A/1614A – Sector Address Table

| Plane | Sector | Size (Bytes/Words) | x8 | x16 |
|-------|--------|--------------------|---------------------------|--------------------------|
| | | | Address Range (A19 - A-1) | Address Range (A19 - A0) |
| A | SA0 | 8K/4K | 000000 - 001FFF | 00000 - 00FFF |
| A | SA1 | 8K/4K | 002000 - 003FFF | 01000 - 01FFF |
| A | SA2 | 8K/4K | 004000 - 005FFF | 02000 - 02FFF |
| A | SA3 | 8K/4K | 006000 - 007FFF | 03000 - 03FFF |
| A | SA4 | 8K/4K | 008000 - 009FFF | 04000 - 04FFF |
| A | SA5 | 8K/4K | 00A000 - 00BFFF | 05000 - 05FFF |
| A | SA6 | 8K/4K | 00C000 - 00DFFF | 06000 - 06FFF |
| A | SA7 | 8K/4K | 00E000 - 00FFFF | 07000 - 07FFF |
| A | SA8 | 64K/32K | 010000 - 01FFFF | 08000 - 0FFFF |
| A | SA9 | 64K/32K | 020000 - 02FFFF | 10000 - 17FFF |
| A | SA10 | 64K/32K | 030000 - 03FFFF | 18000 - 1FFFF |
| A | SA11 | 64K/32K | 040000 - 04FFFF | 20000 - 27FFF |
| A | SA12 | 64K/32K | 050000 - 05FFFF | 28000 - 2FFFF |
| A | SA13 | 64K/32K | 060000 - 06FFFF | 30000 - 37FFF |
| A | SA14 | 64K/32K | 070000 - 07FFFF | 38000 - 3FFFF |
| B | SA15 | 64K/32K | 080000 - 08FFFF | 40000 - 47FFF |
| B | SA16 | 64K/32K | 090000 - 09FFFF | 48000 - 4FFFF |
| B | SA17 | 64K/32K | 0A0000 - 0AFFFF | 50000 - 57FFF |
| B | SA18 | 64K/32K | 0B0000 - 0BFFFF | 58000 - 5FFFF |
| B | SA19 | 64K/32K | 0C0000 - 0CFFFF | 60000 - 67FFF |
| B | SA20 | 64K/32K | 0D0000 - 0DFFFF | 68000 - 6FFFF |
| B | SA21 | 64K/32K | 0E0000 - 0EFFFF | 70000 - 77FFF |
| B | SA22 | 64K/32K | 0F0000 - 0FFFFF | 78000 - 7FFFF |
| B | SA23 | 64K/32K | 100000 - 10FFFF | 80000 - 87FFF |
| B | SA24 | 64K/32K | 110000 - 11FFFF | 88000 - 8FFFF |
| B | SA25 | 64K/32K | 120000 - 12FFFF | 90000 - 97FFF |
| B | SA26 | 64K/32K | 130000 - 13FFFF | 98000 - 9FFFF |
| B | SA27 | 64K/32K | 140000 - 14FFFF | A0000 - A7FFF |
| B | SA28 | 64K/32K | 150000 - 15FFFF | A8000 - AFFFF |
| B | SA29 | 64K/32K | 160000 - 16FFFF | B0000 - B7FFF |
| B | SA30 | 64K/32K | 170000 - 1EFFFF | B8000 - F7FFF |
| B | SA31 | 64K/32K | 180000 - 18FFFF | C0000 - C7FFF |
| B | SA32 | 64K/32K | 190000 - 19FFFF | C8000 - CFFFF |
| B | SA33 | 64K/32K | 1A0000 - 1AFFFF | D0000 - D7FFF |
| B | SA34 | 64K/32K | 1B0000 - 1BFFFF | D8000 - DFFFF |
| B | SA35 | 64K/32K | 1C0000 - 1CFFFF | E0000 - E7FFF |
| B | SA36 | 64K/32K | 1D0000 - 1DFFFF | E8000 - EFFFF |
| B | SA37 | 64K/32K | 1E0000 - 1EFFFF | F0000 - F7FFF |
| B | SA38 | 64K/32K | 1F0000 - 1FFFFF | F8000 - FFFFF |

AT49BV/LV1604AT/1614AT – Sector Address Table

| Plane | Sector | Size (Bytes/Words) | x8 | x16 |
|-------|--------|--------------------|---------------------------|--------------------------|
| | | | Address Range (A19 - A-1) | Address Range (A19 - A0) |
| B | SA0 | 64K/32K | 000000 - 00FFFF | 00000 - 07FFF |
| B | SA1 | 64K/32K | 010000 - 01FFFF | 08000 - 0FFFF |
| B | SA2 | 64K/32K | 020000 - 02FFFF | 10000 - 17FFF |
| B | SA3 | 64K/32K | 030000 - 03FFFF | 18000 - 1FFFF |
| B | SA4 | 64K/32K | 040000 - 04FFFF | 20000 - 27FFF |
| B | SA5 | 64K/32K | 050000 - 05FFFF | 28000 - 2FFFF |
| B | SA6 | 64K/32K | 060000 - 06FFFF | 30000 - 37FFF |
| B | SA7 | 64K/32K | 070000 - 07FFFF | 38000 - 3FFFF |
| B | SA8 | 64K/32K | 080000 - 08FFFF | 40000 - 47FFF |
| B | SA9 | 64K/32K | 090000 - 09FFFF | 48000 - 4FFFF |
| B | SA10 | 64K/32K | 0A0000 - 0AFFFF | 50000 - 57FFF |
| B | SA11 | 64K/32K | 0B0000 - 0BFFFF | 58000 - 5FFFF |
| B | SA12 | 64K/32K | 0C0000 - 0CFFFF | 60000 - 67FFF |
| B | SA13 | 64K/32K | 0D0000 - 0DFFFF | 68000 - 6FFFF |
| B | SA14 | 64K/32K | 0E0000 - 0EFFFF | 70000 - 77FFF |
| B | SA15 | 64K/32K | 0F0000 - 0FFFFF | 78000 - 7FFFF |
| B | SA16 | 64K/32K | 100000 - 10FFFF | 80000 - 87FFF |
| B | SA17 | 64K/32K | 110000 - 11FFFF | 88000 - 8FFFF |
| B | SA18 | 64K/32K | 120000 - 12FFFF | 90000 - 97FFF |
| B | SA19 | 64K/32K | 130000 - 13FFFF | 98000 - 9FFFF |
| B | SA20 | 64K/32K | 140000 - 14FFFF | A0000 - A7FFF |
| B | SA21 | 64K/32K | 150000 - 15FFFF | A8000 - AFFFF |
| B | SA22 | 64K/32K | 160000 - 16FFFF | B0000 - B7FFF |
| B | SA23 | 64K/32K | 170000 - 17FFFF | B8000 - BFFFF |
| A | SA24 | 64K/32K | 180000 - 18FFFF | C0000 - C7FFF |
| A | SA25 | 64K/32K | 190000 - 19FFFF | C8000 - CFFFF |
| A | SA26 | 64K/32K | 1A0000 - 1AFFFF | D0000 - D7FFF |
| A | SA27 | 64K/32K | 1B0000 - 1BFFFF | D8000 - DFFFF |
| A | SA28 | 64K/32K | 1C0000 - 1CFFFF | E0000 - E7FFF |
| A | SA29 | 64K/32K | 1D0000 - 1DFFFF | E8000 - EFFFF |
| A | SA30 | 64K/32K | 1E0000 - 1EFFFF | F0000 - F7FFF |
| A | SA31 | 8K/4K | 1F0000 - 1F1FFF | F8000 - F8FFF |
| A | SA32 | 8K/4K | 1F2000 - 1F3FFF | F9000 - F9FFF |
| A | SA33 | 8K/4K | 1F4000 - 1F5FFF | FA000 - FAFFF |
| A | SA34 | 8K/4K | 1F6000 - 1F7FFF | FB000 - FBFFF |
| A | SA35 | 8K/4K | 1F8000 - 1F9FFF | FC000 - FCFFF |
| A | SA36 | 8K/4K | 1FA000 - 1FBFFF | FD000 - FDFFF |
| A | SA37 | 8K/4K | 1FC000 - 1FDFFF | FE000 - FEFFF |
| A | SA38 | 8K/4K | 1FE000 - 1FFFFF | FF000 - FFFFF |



DC and AC Operating Range

| | | AT49BV/LV16X4A(T)-70 | AT49BV/LV16X4A(T)-90 |
|------------------------------|------|----------------------------|----------------------------|
| Operating Temperature (Case) | Ind. | -40°C - 85°C | -40°C - 85°C |
| V _{CC} Power Supply | | 2.65V to 3.3V/3.0V to 3.6V | 2.65V to 3.3V/3.0V to 3.6V |

Operating Modes

| Mode | \overline{CE} | \overline{OE} | \overline{WE} | \overline{RESET} | V _{PP} | Ai | I/O |
|------------------------------|-----------------|------------------|-----------------|--------------------|--------------------------------|----------------------------------------------------------------------------------------|----------------------------------|
| Read | V _{IL} | V _{IL} | V _{IH} | V _{IH} | X | Ai | D _{OUT} |
| Program/Erase ⁽²⁾ | V _{IL} | V _{IH} | V _{IL} | V _{IH} | V _{PP} ⁽⁶⁾ | Ai | D _{IN} |
| Standby/Program Inhibit | V _{IH} | X ⁽¹⁾ | X | V _{IH} | X | X | High-Z |
| Program Inhibit | X | X | V _{IH} | V _{IH} | X | | |
| | X | V _{IL} | X | V _{IH} | X | | |
| Output Disable | X | V _{IH} | X | V _{IH} | X | | High-Z |
| Reset | X | X | X | V _{IL} | X | X | High-Z |
| Product Identification | | | | | | | |
| Hardware | V _{IL} | V _{IL} | V _{IH} | V _{IH} | | A1 - A19 = V _{IL} , A9 = V _H ⁽³⁾ , A0 = V _{IL} | Manufacturer Code ⁽⁴⁾ |
| | | | | | | A1 - A19 = V _{IL} , A9 = V _H ⁽³⁾ , A0 = V _{IH} | Device Code ⁽⁴⁾ |
| Software ⁽⁵⁾ | | | | V _{IH} | | A0 = V _{IL} , A1 - A19 = V _{IL} | Manufacturer Code ⁽⁴⁾ |
| | | | | | | A0 = V _{IH} , A1 - A19 = V _{IL} | Device Code ⁽⁴⁾ |

- Notes:
- X can be V_{IL} or V_{IH}.
 - Refer to AC programming waveforms on page 19.
 - V_H = 12.0V ± 0.5V.
 - Manufacturer Code: 1FH (x8); 001FH (x16), Device Code: C0H (x8)-AT49BV/LV16X4A; 00C0H (x16)-AT49BV/LV16X4A; C2H (x8)-AT49BV/LV16X4AT; 00C2H (x16)-AT49BV/LV16X4T.
 - See details under "Software Product Identification Entry/Exit" on page 20.
 - V_{PP} can be left unconnected or 0V ≤ V_{PP} ≤ 3.3V. For faster erase/program operations, V_{PP} can be set to 5.0V ± 0.5V or 12V ± 0.5V.

DC Characteristics

| Symbol | Parameter | Condition | Min | Max | Units |
|-------------------|------------------------------------------------------------|-------------------------------------------------------|----------------------------------|------|---------|
| I_{LI} | Input Load Current | $V_{IN} = 0V$ to V_{CC} | | 10 | μA |
| I_{LO} | Output Leakage Current | $V_{I/O} = 0V$ to V_{CC} | | 10 | μA |
| I_{SB1} | V_{CC} Standby Current CMOS | $\overline{CE} = V_{CC} - 0.3V$ to V_{CC} | | 10 | μA |
| I_{SB2} | V_{CC} Standby Current TTL | $\overline{CE} = 2.0V$ to V_{CC} | | 1 | mA |
| I_{SB3} | V_{CC} Standby Current TTL | $\overline{CE} = 2.0V$ to V_{CC} , $V_{CC} = 2.85V$ | | 10 | μA |
| $I_{CC}^{(1)(2)}$ | V_{CC} Active Read Current | $f = 5$ MHz; $I_{OUT} = 0$ mA, $3.3V \leq V_{CC}$ | | 30 | mA |
| I_{CC1} | V_{CC} Programming Current ($V_{PP} = V_{CC}$) | | | 45 | mA |
| I_{PP1} | V_{PP} Input Load Current | $V_{PP} = 0V$, $V_{CC} = 3.0V$ | | 10 | μA |
| | | $V_{PP} = V_{CC} = 3.0V$ | | 10 | μA |
| I_{CC2} | V_{CC} Programming Current ($V_{PP} = 5.0V \pm 0.5V$) | | | 40 | mA |
| I_{PP2} | V_{PP} Programming Current ($V_{PP} = 5.0V \pm 0.5V$) | | | 5 | mA |
| I_{CC3} | V_{CC} Programming Current ($V_{PP} = 12.0V \pm 0.5V$) | | | 40 | mA |
| I_{PP3} | V_{PP} Programming Current ($V_{PP} = 12.0V \pm 0.5V$) | | | 6 | mA |
| V_{IL} | Input Low Voltage | | | 0.6 | V |
| V_{IH} | Input High Voltage | | 2.0 | | V |
| V_{OL1} | Output Low Voltage | $I_{OL} = 2.1$ mA | | 0.45 | V |
| V_{OL2} | Output Low Voltage | $I_{OL} = 1.0$ mA | | 0.20 | V |
| V_{OH1} | Output High Voltage | $I_{OH} = -400$ μA $V_{CCQ} < 2.6V$ | $V_{CCQ} - 0.2$ [AT49BV1604A(T)] | | V |
| | | $I_{OH} = -400$ μA $V_{CCQ} \geq 2.6V$ | 2.4 [AT49BV1604A(T)] | | V |
| | | $I_{OH} = -400$ μA | 2.4 [AT49BV/LV1614A(T)] | | V |
| V_{OH2} | Output High Voltage | $I_{OH} = -100$ μA $V_{CCQ} < 2.6V$ | $V_{CCQ} - 0.1$ [AT49BV1604A(T)] | | V |
| | | $I_{OH} = -100$ μA $V_{CCQ} \geq 2.6V$ | 2.5 [AT49BV1604A(T)] | | V |
| | | $I_{OH} = -100$ μA | 2.5 [AT49BV/LV1614A(T)] | | V |

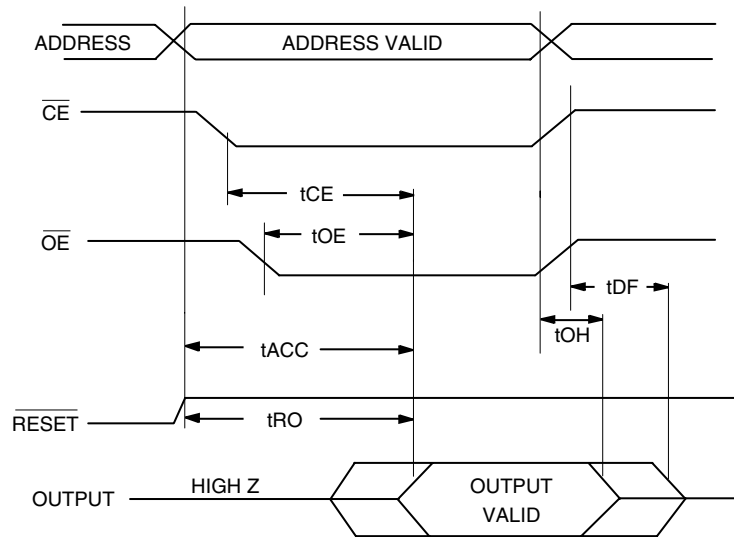
- Note:
1. In the erase mode, I_{CC} is 50 mA.
 2. For $3.3V < V_{CC} < 3.6V$, I_{CC} (max) = 35 mA.



AC Read Characteristics

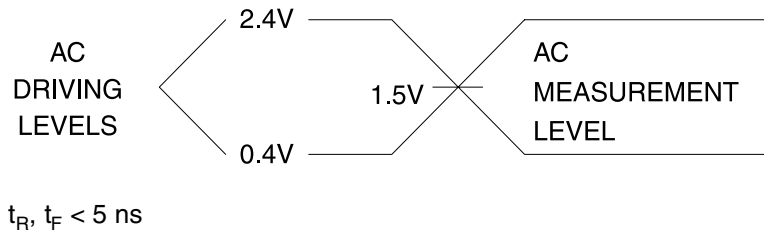
| Symbol | Parameter | AT49BV/LV16X4A(T)-70 | | AT49BV/LV16X4A(T)-90 | | Units |
|-------------------|-----------------------------------------------------------------------------------------|----------------------|-----|----------------------|-----|-------|
| | | Min | Max | Min | Max | |
| t_{ACC} | Address to Output Delay | | 70 | | 90 | ns |
| $t_{CE}^{(1)}$ | \overline{CE} to Output Delay | | 70 | | 90 | ns |
| $t_{OE}^{(2)}$ | \overline{OE} to Output Delay | 0 | 35 | 0 | 40 | ns |
| $t_{DF}^{(3)(4)}$ | \overline{CE} or \overline{OE} to Output Float | 0 | 25 | 0 | 25 | ns |
| t_{OH} | Output Hold from \overline{OE} , \overline{CE} or Address, whichever occurred first | 0 | | 0 | | ns |
| t_{RO} | \overline{RESET} to Output Delay | | 100 | | 100 | ns |

AC Read Waveforms⁽¹⁾⁽²⁾⁽³⁾⁽⁴⁾

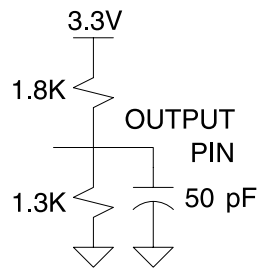


- \overline{CE} may be delayed up to $t_{ACC} - t_{CE}$ after the address transition without impact on t_{ACC} .
- \overline{OE} may be delayed up to $t_{CE} - t_{OE}$ after the falling edge of \overline{CE} without impact on t_{CE} or by $t_{ACC} - t_{OE}$ after an address change without impact on t_{ACC} .
- t_{DF} is specified from \overline{OE} or \overline{CE} , whichever occurs first (CL = 5 pF).
- This parameter is characterized and is not 100% tested.

Input Test Waveforms and Measurement Level



Output Test Load



Pin Capacitance

$f = 1 \text{ MHz}, T = 25^\circ\text{C}^{(1)}$

| Symbol | Typ | Max | Units | Conditions |
|-----------|-----|-----|-------|----------------|
| C_{IN} | 4 | 6 | pF | $V_{IN} = 0V$ |
| C_{OUT} | 8 | 12 | pF | $V_{OUT} = 0V$ |

Note: 1. This parameter is characterized and is not 100% tested.

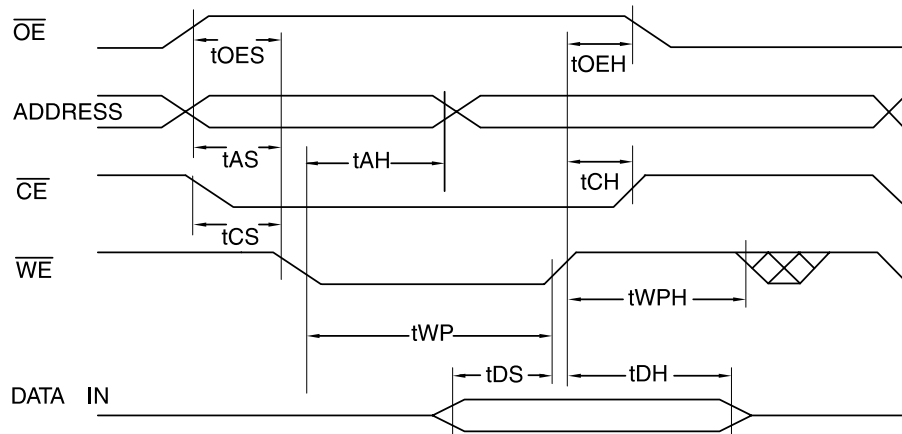


AC Byte/Word Load Characteristics

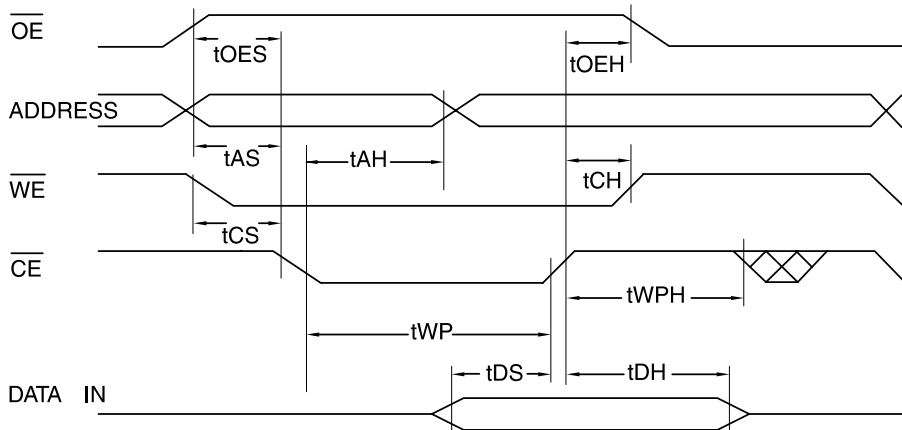
| Symbol | Parameter | Min | Max | Units |
|-------------------|----------------------------------------------------------|-----|-----|-------|
| t_{AS}, t_{OES} | Address, \overline{OE} Setup Time | 0 | | ns |
| t_{AH} | Address Hold Time | 40 | | ns |
| t_{CS} | Chip Select Setup Time | 0 | | ns |
| t_{CH} | Chip Select Hold Time | 0 | | ns |
| t_{WP} | Write Pulse Width (\overline{WE} or \overline{CE}) | 40 | | ns |
| t_{DS} | Data Setup Time | 30 | | ns |
| t_{DH}, t_{OEH} | Data, \overline{OE} Hold Time | 0 | | ns |
| t_{WPH} | Write Pulse Width High | 30 | | ns |

AC Byte/Word Load Waveforms

\overline{WE} Controlled



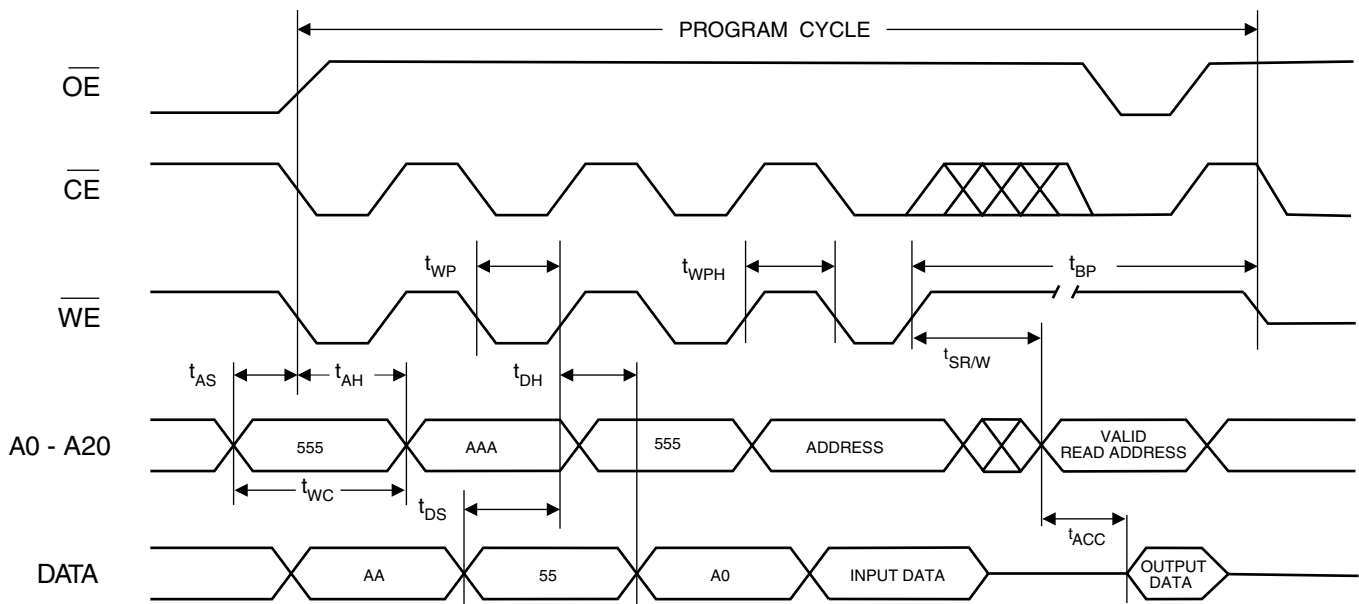
\overline{CE} Controlled



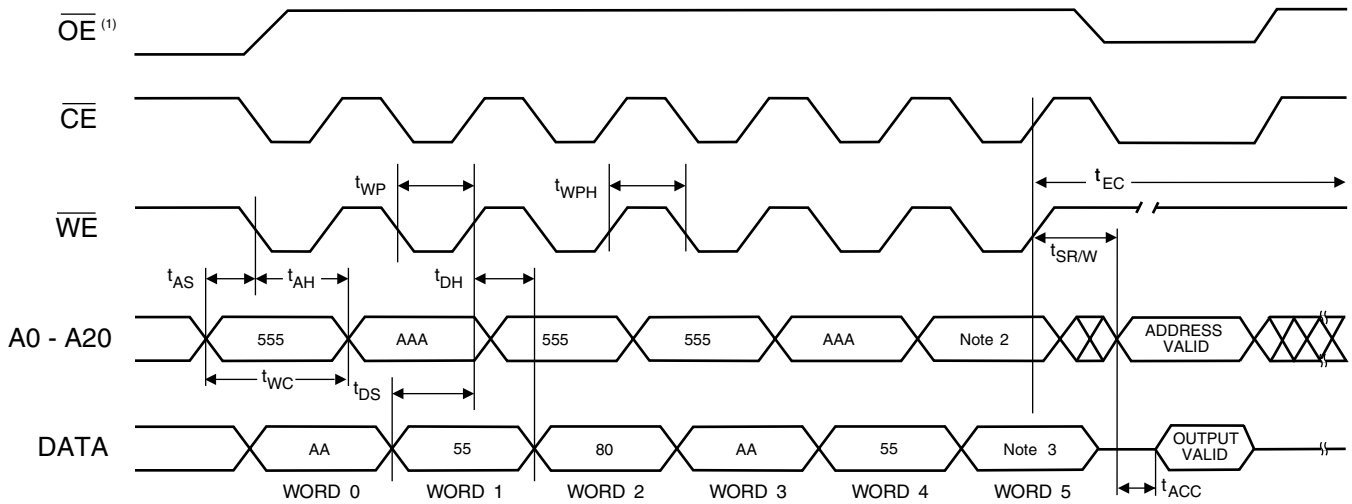
Program Cycle Characteristics

| Symbol | Parameter | Min | Typ | Max | Units |
|-------------|-----------------------------------------------------|-----|-----|-----|---------|
| t_{BP} | Byte/Word Programming Time ($0V < V_{PP} < 4.5V$) | | 20 | 50 | μs |
| t_{BPVPP} | Byte/Word Programming Time ($V_{PP} \geq 4.5V$) | | 10 | 25 | μs |
| t_{AS} | Address Setup Time | 0 | | | ns |
| t_{AH} | Address Hold Time | 40 | | | ns |
| t_{DS} | Data Setup Time | 30 | | | ns |
| t_{DH} | Data Hold Time | 0 | | | ns |
| t_{WP} | Write Pulse Width | 40 | | | ns |
| t_{WPH} | Write Pulse Width High | 30 | | | ns |
| t_{WC} | Write Cycle Time | 70 | | | ns |
| t_{SRW} | Latency between Read and Write Operations | 50 | | | ns |
| t_{RP} | $\overline{\text{Reset}}$ Pulse Width | 500 | | | ns |
| t_{RH} | $\overline{\text{Reset}}$ High Time before Read | 50 | | | ns |
| t_{EC} | Chip Erase Cycle Time ($V_{PP} < 4.5V$) | | | 12 | seconds |
| t_{ECVPP} | Chip Erase Cycle Time ($V_{PP} \geq 4.5V$) | | | 6 | seconds |
| t_{SEC} | Sector Erase Cycle Time ($V_{PP} < 4.5V$) | | 300 | 400 | ms |
| t_{EPS} | Erase or Program Suspend Time | | | 15 | μs |

Program Cycle Waveforms



Sector or Chip Erase Cycle Waveforms



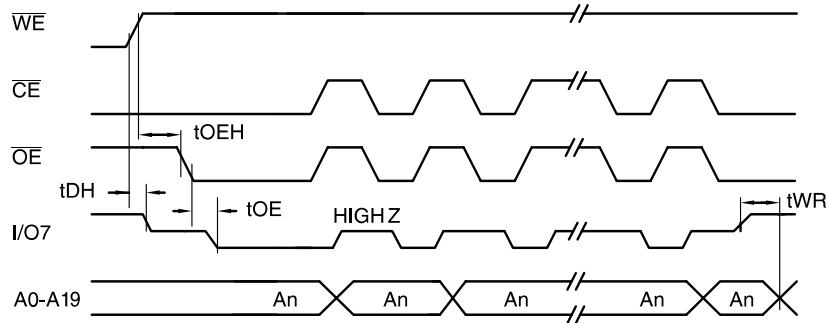
- Notes:
- \overline{OE} must be high only when \overline{WE} and \overline{CE} are both low.
 - For chip erase, the address should be 555. For sector erase, the address depends on what sector is to be erased. (See note 3 under Command Definitions.)
 - For chip erase, the data should be 10H, and for sector erase, the data should be 30H.

Data Polling Characteristics⁽¹⁾

| Symbol | Parameter | Min | Typ | Max | Units |
|-----------------|-------------------------------------------------|-----|-----|-----|-------|
| t_{DH} | Data Hold Time | 10 | | | ns |
| $t_{OE\bar{H}}$ | $\bar{O}\bar{E}$ Hold Time | 10 | | | ns |
| t_{OE} | $\bar{O}\bar{E}$ to Output Delay ⁽²⁾ | | | | ns |
| t_{WR} | Write Recovery Time | 0 | | | ns |

Notes: 1. These parameters are characterized and not 100% tested.
2. See t_{OE} spec in "AC Read Characteristics" on page 14.

Data Polling Waveforms

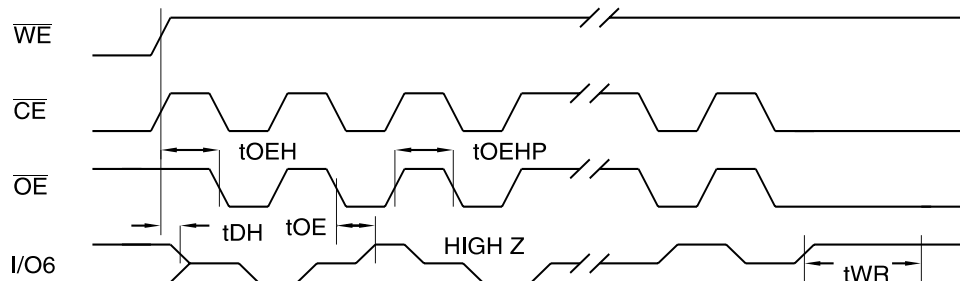


Toggle Bit Characteristics⁽¹⁾

| Symbol | Parameter | Min | Typ | Max | Units |
|-----------------|-------------------------------------------------|-----|-----|-----|-------|
| t_{DH} | Data Hold Time | 10 | | | ns |
| $t_{OE\bar{H}}$ | $\bar{O}\bar{E}$ Hold Time | 10 | | | ns |
| t_{OE} | $\bar{O}\bar{E}$ to Output Delay ⁽²⁾ | | | | ns |
| t_{OEHP} | $\bar{O}\bar{E}$ High Pulse | 50 | | | ns |
| t_{WR} | Write Recovery Time | 0 | | | ns |

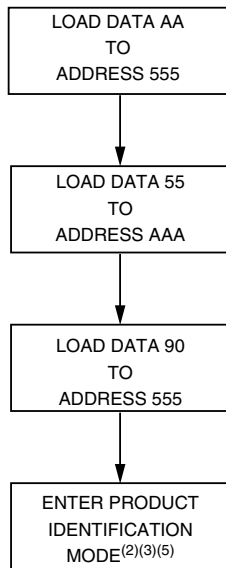
Notes: 1. These parameters are characterized and not 100% tested.
2. See t_{OE} spec in "AC Read Characteristics" on page 14.

Toggle Bit Waveforms⁽¹⁾⁽²⁾⁽³⁾

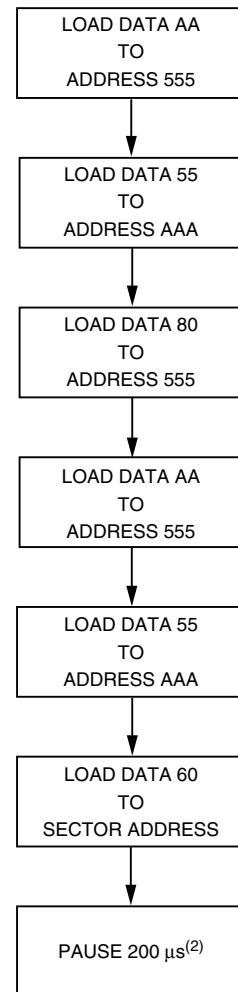


Notes: 1. Toggling either $\bar{O}\bar{E}$ or $\bar{C}\bar{E}$ or both $\bar{O}\bar{E}$ and $\bar{C}\bar{E}$ will operate toggle bit. The t_{OEHP} specification must be met by the toggling input(s).
2. Beginning and ending state of I/O6 will vary.
3. Any address location may be used but the address should not vary.

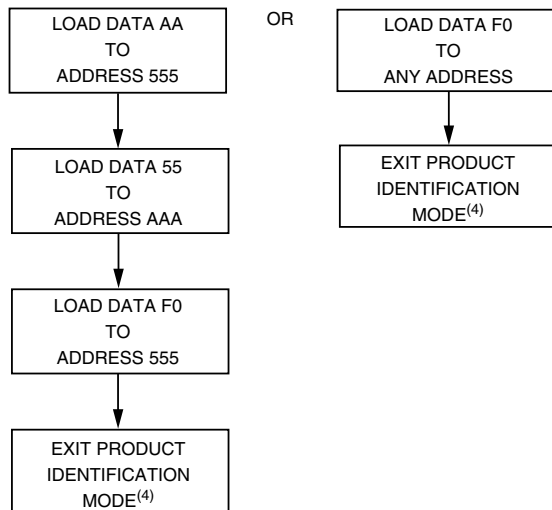
Software Product Identification Entry⁽¹⁾



Sector Lockdown Enable Algorithm⁽¹⁾



Software Product Identification Exit⁽¹⁾⁽⁶⁾



- Notes:
1. Data Format: I/O15 - I/O8 (Don't Care); I/O7 - I/O0 (Hex)
Address Format: A11 - A0 (Hex), A-1, and A11 - A19 (Don't Care).
 2. Sector Lockdown feature enabled.

- Notes:
1. Data Format: I/O15 - I/O8 (Don't Care); I/O7 - I/O0 (Hex)
Address Format: A11 - A0 (Hex), A-1, and A11 - A19 (Don't Care).
 2. A1 - A19 = V_{IL}. Manufacturer Code is read for A0 = V_{IL}; Device Code is read for A0 = V_{IH}.
Additional Device Code is read for address 0003H
 3. The device does not remain in identification mode if powered down.
 4. The device returns to standard operation mode.
 5. Manufacturer Code: 1FH(x8); 001FH(x16)
Device Code: C0H (x8) - AT49BV/LV16X4A;
00C0H (x16) - AT49BV/LV16X4A;
C2H (x8) - AT49BV/LV16X4AT;
00C2H (x16) - AT49BV/LV16X4AT.
Additional Device Code: C8H (x8) - AT49BV/LV16X4A(T)
00C8H (x16) - AT49BV/LV16X4A(T)
 6. Either one of the Product ID Exit commands can be used.

Status Bit Table

| | Status Bit | | | | | |
|---------------------------------------------------------|-------------------|-------------------|---------|---------|---------|---------|
| | I/O7 | | I/O6 | | I/O2 | |
| Read Address In | Plane A | Plane B | Plane A | Plane B | Plane A | Plane B |
| While | | | | | | |
| Programming in Plane A | $\overline{I/O7}$ | DATA | TOGGLE | DATA | 1 | DATA |
| Programming in Plane B | DATA | $\overline{I/O7}$ | DATA | TOGGLE | DATA | 1 |
| Erasing in Plane A | 0 | DATA | TOGGLE | DATA | TOGGLE | DATA |
| Erasing in Plane B | DATA | 0 | DATA | TOGGLE | DATA | TOGGLE |
| Erase Suspended & Read Erasing Sector | 1 | 1 | 1 | 1 | TOGGLE | TOGGLE |
| Erase Suspended & Read Non-erasing Sector | DATA | DATA | DATA | DATA | DATA | DATA |
| Erase Suspended & Program Non-erasing Sector in Plane A | $\overline{I/O7}$ | DATA | TOGGLE | DATA | TOGGLE | DATA |
| Erase Suspended & Program Non-erasing Sector in Plane B | DATA | $\overline{I/O7}$ | DATA | TOGGLE | DATA | TOGGLE |



AT49BV1604A(T)/1614A(T) Ordering Information

| t _{ACC} (ns) | I _{CC} (mA) | | Ordering Code | Package | Operation Range |
|--------------------------|----------------------|---------|----------------------------------------|-------------|------------------------------|
| | Active | Standby | | | |
| 70 | 25 | 0.01 | AT49BV1604A-70CI AT49BV1604A-70TI | 45C1 48T | Industrial (-40° to 85°C) |
| 90 | 25 | 0.01 | AT49BV1604A-90CI AT49BV1604A-90TI | 45C1 48T | Industrial (-40° to 85°C) |
| 70 | 25 | 0.01 | AT49BV1604AT-70CI AT49BV1604AT-70TI | 45C1 48T | Industrial (-40° to 85°C) |
| 90 | 25 | 0.01 | AT49BV1604AT-90CI AT49BV1604AT-90TI | 45C1 48T | Industrial (-40° to 85°C) |
| 70 | 25 | 0.01 | AT49BV1614A-70CI AT49BV1614A-70TI | 48C5 48T | Industrial (-40° to 85°C) |
| 90 | 25 | 0.01 | AT49BV1614A-90CI AT49BV1614A-90TI | 48C5 48T | Industrial (-40° to 85°C) |
| 70 | 25 | 0.01 | AT49BV1614AT-70CI AT49BV1614AT-70TI | 48C5 48T | Industrial (-40° to 85°C) |
| 90 | 25 | 0.01 | AT49BV1614AT-90CI AT49BV1614AT-90TI | 48C5 48T | Industrial (-40° to 85°C) |

AT49LV1614A(T) Ordering Information

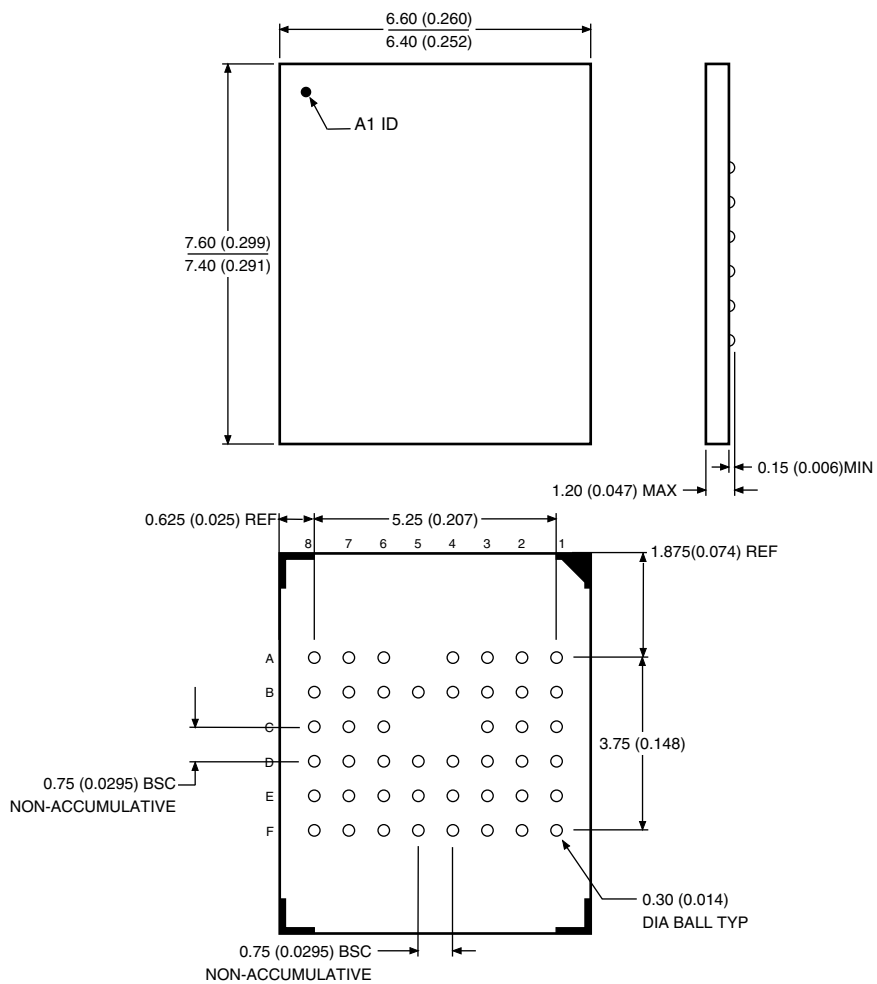
| t _{ACC} (ns) | I _{CC} (mA) | | Ordering Code | Package | Operation Range |
|--------------------------|----------------------|---------|----------------------------------------|-------------|------------------------------|
| | Active | Standby | | | |
| 70 | 25 | 0.01 | AT49LV1614A-70CI AT49LV1614A-70TI | 48C5 48T | Industrial (-40° to 85°C) |
| 70 | 25 | 0.01 | AT49LV1614AT-70CI AT49LV1614AT-70TI | 48C5 48T | Industrial (-40° to 85°C) |

| Package Type | |
|--------------|-----------------------------------------------------------|
| 45C1 | 45-ball, Plastic Chip-size Ball Grid Array Package (CBGA) |
| 48C5 | 48-ball, Plastic Chip-size Ball Grid Array Package (CBGA) |
| 48T | 48-lead, Plastic Thin Small Outline Package (TSOP) |

Packaging Information

45C1 – CBGA

Dimensions in Millimeters and (Inches).
Controlling dimension: millimeters.



4/11/01



2325 Orchard Parkway
San Jose, CA 95131

TITLE

45C1, 45-ball (8 x 6 Array), 0.75 mm Pitch, 6.5 x 7.5 x 1.2 mm
Chip-scale Ball Grid Array Package (CBGA)

DRAWING NO.

45C1

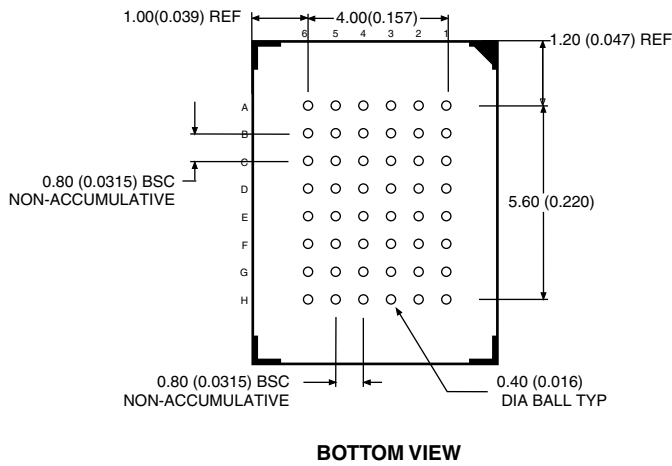
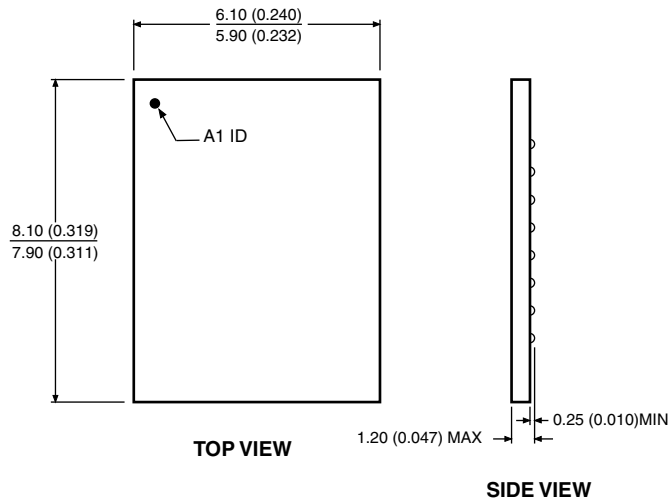
REV.

A



48C5 – CBGA

Dimensions in Millimeters and (Inches).
Controlling dimension: millimeters.



10/18/01



2325 Orchard Parkway
San Jose, CA 95131

TITLE

48C5, 48-ball (6 x 8 Array), 0.80 mm Pitch, 6 x 8 x 1.2 mm
Chip-scale Ball Grid Array Package (CBGA)

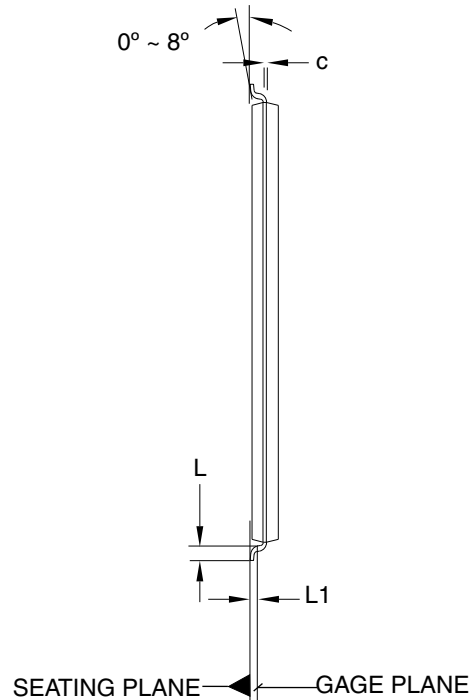
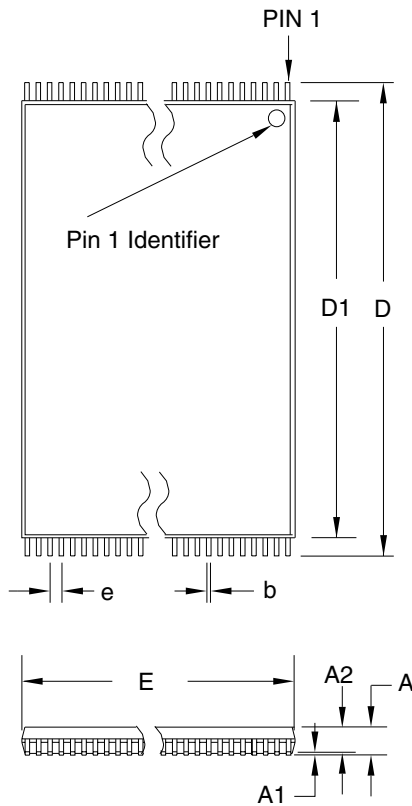
DRAWING NO.

48C5

REV.

A

48T – TSOP



COMMON DIMENSIONS
(Unit of Measure = mm)

| SYMBOL | MIN | NOM | MAX | NOTE |
|--------|------------|-------|-------|--------|
| A | – | – | 1.20 | |
| A1 | 0.05 | – | 0.15 | |
| A2 | 0.95 | 1.00 | 1.05 | |
| D | 19.80 | 20.00 | 20.20 | |
| D1 | 18.30 | 18.40 | 18.50 | Note 2 |
| E | 11.90 | 12.00 | 12.10 | Note 2 |
| L | 0.50 | 0.60 | 0.70 | |
| L1 | 0.25 BASIC | | | |
| b | 0.17 | 0.22 | 0.27 | |
| c | 0.10 | – | 0.21 | |
| e | 0.50 BASIC | | | |

- Notes:
1. This package conforms to JEDEC reference MO-142, Variation DD.
 2. Dimensions D1 and E do not include mold protrusion. Allowable protrusion on E is 0.15 mm per side and on D1 is 0.25 mm per side.
 3. Lead coplanarity is 0.10 mm maximum.

10/18/01



2325 Orchard Parkway
San Jose, CA 95131

TITLE

48T, 48-lead (12 x 20 mm Package) Plastic Thin Small Outline Package, Type I (TSOP)

DRAWING NO.

48T

REV.

B



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